Silicon N Channel Power MOSFET

Description

The HXN1008 is n-channel power trench MOSFET with latest technology. So fast switching speed and low on-resistance. Usually used at power switching application . It is also intended for any applications with low gate drive requirements .

Features

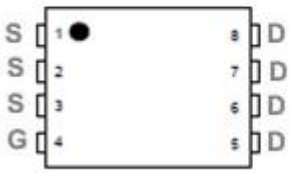
- Latest Trench Power MOSFET technology
- Low On-state Resistance
- High Current Density
- Low Gate Charge
- 100% UIS Test

Product Summary

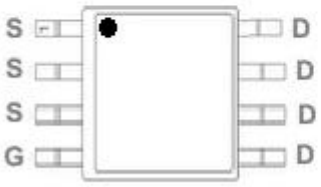
BVDS	RDSON	ID
100V	22mΩ	8A

Applications

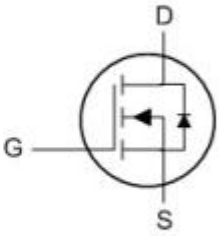
- Power Management
- Motor Driver



DFN5*6



SOP8



1、Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage (V_{GS} = 0)	100	V
V_{GS}	Gate-source voltage	±20	V
I_D(1)	Drain current (continuous) at TC = 25℃	8	A
I_{DM}(2)	Drain current (pulsed)	32	A
P_D	Power dissipation at TC = 25℃	2.0	W
E_{AS}(3)	Single pulse avalanche energy	400	mJ
Tj	Operating junction temperature	-55 to 150	℃

1. Current limited by package
2. Pulse width limited by safe operating area
3. Starting Tj= 25 ℃， ID= 28A, VDD= 30V，L=1mH

2、Thermal data

Symbol	Parameter	Min.	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient		60		℃/ W
$R_{\theta JC}$	Thermal Resistance Junction-Case		20		℃/ W

3、Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown	I_D=250μA, V_{GS}= 0	100			V
I_{DSS}	Zero gate voltage drain	V_{DS}=Max rating			1	μA
I_{GSS}	Gate body leakage current	V_{GS} =±20V			±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS}= V_{GS}	1	1.6	2.5	V
$R_{DS(on)}$	Static drain-source on	V_{GS}= 10V ，Id=8A		16	18	mΩ
$R_{DS(on)}$	Static drain-source on	V_{GS}= 4.5V ，Id=6A		20	22	mΩ

C_{iss}	Input capacitance	V_{DS} =25V		3800		pF
C_{oss}	Output capacitance	f = 1 MHz		230		pF
C_{rss}	Reverse transfer	V_{GS} = 0		200		pF
Q_g	Total gate charge	V_{DD} = 30V		60		nC
Q_{gs}	Gate-source charge	I_D = 40A		15		nC
Q_{gd}	Gate-drain charge	V_{GS} =10V		10		nC
I_{SD}	Source-drain current				65	A
I_{SDM}(1)	Source-drain current (pulsed)				260	A
V_{SD}(2)	Forward on voltage	I_{SD} = 8A, V_{GS} = 0			1.2	V

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300μs, duty cycle 1.5%